

2SD1258

Silicon NPN triple diffusion planar type

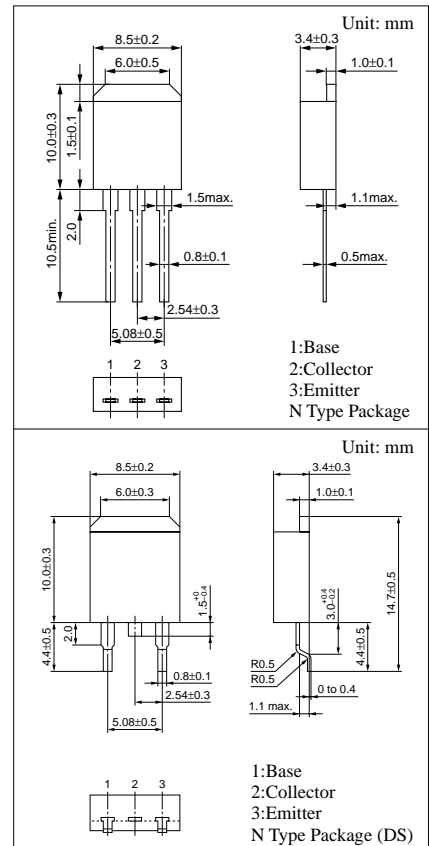
For power amplification with high forward current transfer ratio

Features

- High forward current transfer ratio h_{FE}
- Satisfactory linearity of forward current transfer ratio h_{FE}
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit	
Collector to base voltage	V_{CBO}	200	V	
Collector to emitter voltage	V_{CEO}	150	V	
Emitter to base voltage	V_{EBO}	6	V	
Peak collector current	I_{CP}	2.5	A	
Collector current	I_C	1	A	
Base current	I_B	0.1	A	
Collector power dissipation	P_C	$T_C=25^\circ\text{C}$	40	W
		$T_a=25^\circ\text{C}$	1.3	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	



Electrical Characteristics ($T_C=25^\circ\text{C}$)

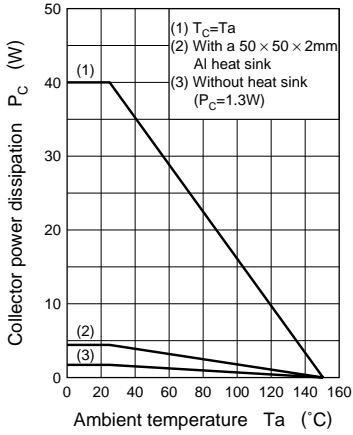
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 200\text{V}, I_E = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$			100	μA
Collector to emitter voltage	V_{CEO}	$I_C = 25\text{mA}, I_B = 0$	150			V
Forward current transfer ratio	h_{FE}^*	$V_{CE} = 4\text{V}, I_C = 0.2\text{A}$	500		2000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 0.5\text{A}, I_B = 0.02\text{A}$			1	V
Transition frequency	f_T	$V_{CE} = 4\text{V}, I_C = 0.1\text{A}, f = 10\text{MHz}$		25		MHz

* h_{FE} Rank classification

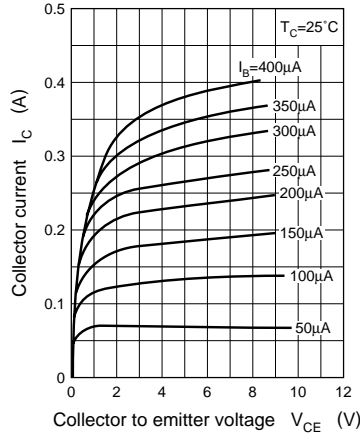
Rank	Q	P
h_{FE}	500 to 1200	800 to 2000

Note: Ordering can be made by the common rank (PQ rank $h_{FE} = 500$ to 2000) in the rank classification.

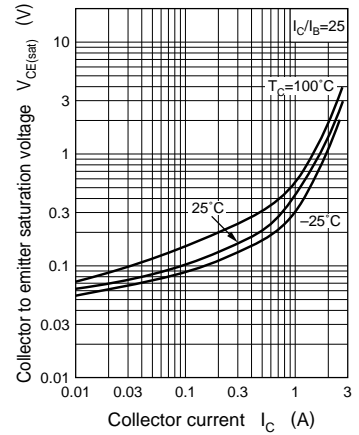
$P_C - T_a$



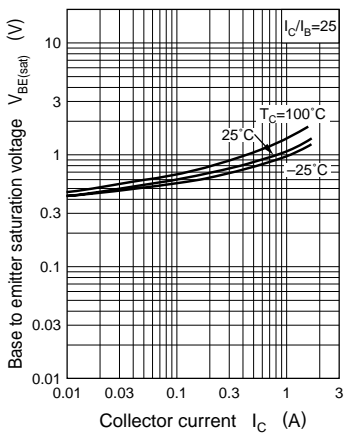
$I_C - V_{CE}$



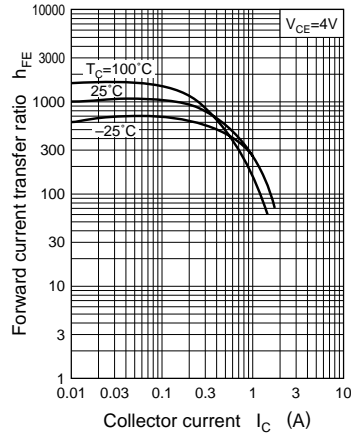
$V_{CE(sat)} - I_C$



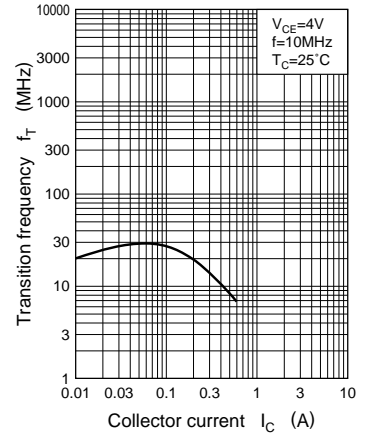
$V_{BE(sat)} - I_C$



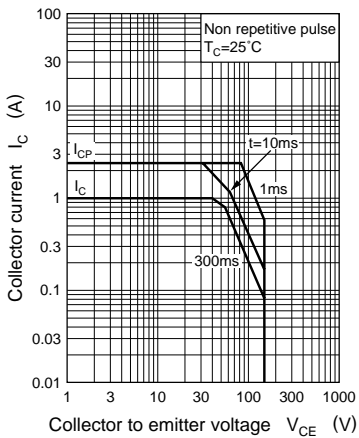
$h_{FE} - I_C$



$f_T - I_C$



Area of safe operation (ASO)



$R_{th(t)} - t$

